

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	218	ajika.in. and natsuo.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:23
S2	145	shukuri.in. and shoji.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:23
S3	252	mihara.in. and masaaki.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:23
S4	0	nakashima.in. and "moriyoshi.in"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:24
S5	0	((programming adj bit adj data) and (nonvolatile adj semiconductor adj memory) and (n adj type adj well) and (charge adj accumulation) and (nano \$1crystal adj layer) and (nonconductive adj charge adj trap) and (tunnel adj2 insulating) and (Vg> Vsub> Vs> Vd) and (Vg-Vd) and (potential adj difference) and band and (hot adj electrons)).dm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:31

S6	1	((programming adj bit adj data) and (nonvolatile adj semiconductor adj memory) and (n adj type adj well) and (charge adj accumulation) and (nano \$1crystal adj layer) and (nonconductive adj charge adj trap) and (tunnel adj2 insulating) and (potential adj difference) and band and (hot adj electrons)). c1m.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:31
S7	304171	(nonvolatile or (non-volatile) or (non adj volatile) adj3 memory) and (program\$4 or stor\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:34
S8	11017	S7 and (type adj2 well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:34
S9	16295	S7 and (type near2 well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:34
S10	917	S9 and charge near4 accumula\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:35
S11	252	S10 and (charge near3 trap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:35
S12	0	S11 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:36

S13	41	S11 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:36
S14	33	S13 and (supply near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:37
S15	29	S13 and (power near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:37
S16	18	S15 and (hot adj2 electron)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:37
S17	18	S16 and inject\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:37
S18	4	S17 and @ad<"20040111"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:38
S19	2208	365/185.28	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41
S20	1864	S19 and (nonvolatile or (non-volatile) or (non adj volatile) adj3 memory) and (program\$4 or stor\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41
S21	406	S20 and (type near2 well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41

S22	74	S21 and charge near4 accumula\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41
S23	39	S22 and (charge near3 trap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41
S24	0	S23 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:41
S25	6	S23 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42
S26	2	S25 and @ad<"20040111"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42
S27	755	365/185.27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42
S28	567	S27 and (nonvolatile or (non-volatile) or (non adj volatile) adj3 memory) and (program\$4 or stor\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42
S29	213	S28 and (type near2 well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42
S30	38	S29 and charge near4 accumula\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:42

S31	9	S30 and (charge near3 trap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S32	1	S31 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S33	0	S32 and @ad<"20040111"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S34	903	365/185.26	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S35	718	S34 and (nonvolatile or (non-volatile) or (non adj volatile) adj3 memory) and (program\$4 or stor\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S36	186	S35 and (type near2 well)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:43
S37	48	S36 and charge near4 accumula\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:44
S38	12	S37 and (charge near3 trap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:44
S39	5	S38 and (substrate near2 voltage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:44

S40	3	S39 and @ad<"20040111"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/30 12:44
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12/30/08 2:00:57 PM

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